| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|---|---|---|---|---|---|---|
| S1 | 0 | "134".ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 15:14 |
| S2 | 38059 | "134"/$.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 15:15 |
| S3 | 5010 | S2 and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 15:15 |
| S4 | 2754 | S3 and particle | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 15:15 |
| S5 | 15224 | S2 and partic$ | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 15:16 |
| S6 | 232 | S5 and (electron adj microscope) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 15:17 |
| S7 | 86 | S6 and (Ti or titaniun or TiN or (titanium adj nitride)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 15:48 |
| S8 | 0 | S7 and HNO | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 15:48 |
| S9 | 18 | S7 and (nitric adj acid) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 15:48 |
| S10 | 0 | S9 and phos | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 15:48 |

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|---|---|---|---|---|---|---|
| S11 | 6 | S9 and acetic | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:03 |
| S12 | 35566 | phosphoric and nitric and acetic | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 13:23 |
| S13 | 1620 | S12 and etch | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:04 |
| S14 | 996 | S13 and ((Ti or titanium or Tin) or titanium adj nitride) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:05 |
| S15 | 570 | S14 and removal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:05 |
| S16 | 476 | S15 and partic$ | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:06 |
| S17 | 220 | S16 and (barrier or liner) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:16 |
| S18 | 4324 | forming adj barrier adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:17 |
| S19 | 1280 | S18 and Ti | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:17 |
| S20 | 2210 | S18 and (Ti ot titanium) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:19 |

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| S21 | 136 | ((forming adj barrier adj layer) and (Ti or titanium)).ab. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:33 |
| S22 | 1 | S21 and (conductor near (poly or polysilicon or silicide or metal)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:31 |
| S23 | 2 | ((forming adj barrier adj layer) and (Ti or titanium)) and particles and rework | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:34 |
| S24 | 3193 | (Ti or titanium) near (particle or paticulate or residual or contaminant or residue) and (rework or removal or etch or remove) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:35 |
| S25 | 1079 | (Ti or titanium) adj (particle or paticulate or residual or contaminant or residue) and (rework or removal or etch or remove) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:36 |
| S26 | 31 | ((Ti or titanium) adj (particle or paticulate or residual or contaminant or residue) and (rework or removal or etch or remove)).ab. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:51 |
| S27 | 118598 | (remove (Ti or titanium) near (substrate or layer)) and barrier | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:53 |
| S28 | 27 | (remove adj (Ti or titanium) near (substrate or layer)) and barrier | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:55 |
| S29 | 77 | (remove adj (Ti or titanium)) near (substrate or layer or barrier) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:57 |
| S30 | 0 | (wet adj etch) near (remove adj (Ti or titanium)) near (substrate or layer or barrier) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:57 |

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| S31 | | 9 | (wet adj etch) and (remove adj (Ti or titanium)) near (substrate or layer or barrier) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 16:59 |
| S32 | | 44 | (remove adj (Ti or titanium)) adj particle | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:01 |
| S33 | | 5 | S32 and etch | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:00 |
| S34 | | 50 | (remove adj (Ti or titanium)) adj (particle or residue or residual or contaminant) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:02 |
| S35 | | 5 | S34 and etch | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:02 |
| S36 | | 50 | remove near (Ti or titanium) near (particle or residue or residual or contaminant) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:03 |
| S37 | | 0 | rework near ((Ti or titanium) near (particle or residue or residual or contaminant)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:03 |
| S38 | | 98 | (rework or remove) near ((Ti or titanium) near (particle or residue or residual or contaminant)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:04 |
| S39 | | 26 | S38 and etch | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:09 |
| S40 | | 5 | ((sulfuric or H2SO4 or sulphate or phated or SO4 or "H.sub.2SO.sub.4" or "H.sub.xSO.sub.x" or "H.sub.nSO. sub.n" or "H.sub.xSO.sub.n" or "H.sub. nSO.sub.x") near rinse) and (Titanium or Ti) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:15 |

| S41 | 8 | ((sulfuric or H2SO4 or sulphate or phated or SO4 or "H.sub.2SO.sub.4" or "H.sub.xSO.sub.x" or "H.sub.nSO.sub.n" or "H.sub.xSO.sub.n" or "H.sub.nSO.sub.x") near rinse) and (corrosion) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:16 |
|-----|------|-----|-----|-----|-----|-----|
| S42 | 0 | ((sulfuric or H2SO4 or sulphate or phated or SO4 or "H.sub.2SO.sub.4" or "H.sub.xSO.sub.x" or "H.sub.nSO.sub.n" or "H.sub.xSO.sub.n" or "H.sub.nSO.sub.x") near rinse) and clean and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:17 |
| S43 | 3084 | sulfuric and clean and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:17 |
| S44 | 6 | sulfuric adj clean and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:19 |
| S45 | 4 | (sulfuric adj acid adj clean) and (Ti or titanium) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:22 |
| S46 | 35 | sulfuric adj acid adj clean | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/23 17:22 |
| S47 | 270 | wafer and reclaim and process | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:20 |
| S48 | 279 | wafer and reclaim and (process or method) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:22 |
| S49 | 50 | S48 and (Titanium or Ti) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:23 |
| S50 | 0 | S49 and H3PO4 and HNO3 and CH3COOH | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:21 |

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| S51 | 14 | (wafer and reclaim and (process or method)).ab. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:22 |
| S52 | 0 | S51 and (titanium or Ti) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:22 |
| S53 | 2146395 | (particle or residual or residue or contaminant) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:24 |
| S54 | 104490 | (Titanium or Ti) and (TiN or (titanuim adj nitide)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:25 |
| S55 | 2214123 | detection or (electrical adj charicteristics) or (electron adj microscope) or map$4 or scan$4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:38 |
| S56 | 233664 | exam or examination | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:28 |
| S60 | 102796 | S56 and S55 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:31 |
| S61 | 48618 | S60 and S53 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:32 |
| S62 | 360920 | S55 and S53 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:32 |
| S63 | 21267 | S62 and S54 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:32 |

| S64 | 2403 | S61 and S54 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:33 |
|-----|------|-------------|------|----|----|------|
| S65 | 21267 | S53 and S55 and S54 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:34 |
| S66 | 4013 | S65 and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:35 |
| S67 | 1309 | S66 and (electron adj microscop$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:35 |
| S68 | 3495 | S66 and semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:36 |
| S69 | 860 | S67 and particles | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:36 |
| S70 | 860 | S67 and particle | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:38 |
| S71 | 48 | S67 and ((detect$$ or find or map$4 or scan$4) near particle) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:40 |
| S72 | 2913 | (particle adj (recogni$4 or detect$4 or find or scan or identifcation)).ab. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:41 |
| S73 | 2044 | (particle adj (recogni$4 or detect$4 or find or scan or identifcation)) and system.ab. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:43 |

| S74 | 1530881 | S73 and wafer or semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:42 |
|-----|---------|---------------------------------|----------------------------------------------|----|----|-------------------|
| S75 | 743 | S73 and (wafer or semiconductor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:42 |
| S76 | 28 | S75 and S54 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:42 |
| S77 | 89 | (particle adj (recogni$4 or detect$4 or find or scan or identifcation)) and (electron adj microscope).ab. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:46 |
| S78 | 25 | (particle adj detection) and (wafer adj fabrication) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:17 |
| S79 | 0 | 2003/0178391 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:54 |
| S80 | 0 | "0178391" and Johnson | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:54 |
| S81 | 0 | 3003/099637 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:56 |
| S82 | 1 | 10/454023 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:57 |
| S83 | 1 | "10421293" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 10:57 |

| S84 | 25 | (particle adj detection) and (wafer adj fabrication) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:29 |
|-----|------|----|----|----|----|----|
| S86 | 644 | particle adj inspection | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:29 |
| S87 | 4870014 | S86 and after process | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:30 |
| S88 | 76 | S86 and ((post or after) near process$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 11:37 |
| S89 | 27 | S88 and electron | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:37 |
| S90 | 17 | S88 and particle.ab. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:38 |
| S91 | 4 | S90 and electron | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:51 |
| S92 | 74 | (rework adj wafer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:51 |
| S93 | 585 | (remove adj barrier adj layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:52 |
| S94 | 0 | S93 and S92 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:51 |

| S95 | 198 | S93 and (Ti or titanuim) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:52 |
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| S96 | 7 | La13 and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:52 |
| S97 | 122 | S95 and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 12:53 |
| S98 | 52 | S97 and defect | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 13:01 |
| S99 | 0 | (titanium or Ti) near electrical adj defect | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 13:02 |
| S100 | 137 | (titanium or Ti) and electrical adj defect | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 13:02 |
| S101 | 35 | (titanium or Ti) and killer adj defect | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 13:15 |
| S102 | 19 | wet adj etch near titanium | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 13:20 |
| S103 | 10 | "5,936,306" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 13:24 |
| S104 | 8 | wet adj etch adj metal adj layers | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 13:25 |

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| S10 5 | 0 | wet adj etch adj metal near (phophoric or H2PO4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 13:26 |
| S10 6 | 0 | wet adj etch adj metal and (phophoric or H2PO4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 13:26 |
| S10 7 | 0 | wet adj etch near metal and (phophoric or H2PO4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 13:26 |
| S10 8 | 3 | wet adj etch and metal and (phophoric or H2PO4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 13:29 |
| S10 9 | 0 | wet adj etch and titanium and (phophoric or H2PO4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 13:42 |
| S11 0 | 36 | (phophoric or H2PO4) and (nitric or HNO3) and (acetic or CH3COOH) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:00 |
| S11 1 | 5 | etch adj rework and wafers | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:08 |
| S11 2 | 258 | etch and rework and titanium | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:08 |
| S11 3 | 756 | rework and titanium | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:09 |
| S11 4 | 0 | rework near titanium | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:08 |

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| S11 5 | 14 | titanium adj nitride and H3PO4 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:16 |
| S11 6 | 1590837 | barrier removal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:17 |
| S11 7 | 309 | barrier adj removal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:17 |
| S11 8 | 10 | etch adj barrier adj removal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:22 |
| S11 9 | 322110 | sulfuric rinse | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:22 |
| S12 0 | 1 | sulfuric adj rinse | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:23 |
| S12 1 | 787025 | sulfuric clean | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:23 |
| S12 2 | 6 | sulfuric adj clean | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:29 |
| S12 3 | 2216 | Schottky adj gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:33 |
| S12 4 | 41 | S123 and Ti and TiN | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:30 |

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| S12 5 | 11 | S124 and schottky.ab. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:30 |
| S12 6 | 4 | S123 and rework | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:37 |
| S12 7 | 285 | barrier adj layer and rework | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:37 |
| S12 8 | 178 | S127 and etch | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:39 |
| S12 9 | 101 | S128 and titanium | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:51 |
| S13 0 | 4 | wet adj etch adj barrier adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:53 |
| S13 1 | 2162 | wet adj etch and barrier adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:53 |
| S13 2 | 1248 | S131 and titanium | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:53 |
| S13 3 | 805 | S132 and titanium adj nitride | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 14:59 |
| S13 4 | 0 | wet near remove near (barrier adj layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 15:00 |

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| S13 5 | 288 | acid and remove near (barrier adj layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 15:00 |
| S13 6 | 680881 | S135 an(ti or titanium)acid and remove near (barrier adj layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 15:01 |
| S13 7 | 204 | S135 and (ti or titanium) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 15:01 |
| S13 8 | 72 | S137 not CMP | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 15:39 |
| S13 9 | 4 | schottky adj gate and two adj level adj metal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 15:43 |
| S14 0 | 3 | "6558739".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 15:51 |
| S14 1 | 2 | "5,338,975".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 15:59 |
| S14 2 | 121 | three adj level adj metal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 15:59 |
| S14 3 | 470 | multi adj level adj metal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 15:59 |
| S14 4 | 187 | S143 and gate | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 15:59 |

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| S14 5 | 81 | S144 and barrier | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 16:00 |
| S14 6 | 68 | S145 and (Titanium or TI) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 16:00 |
| S14 7 | 46 | S146 and wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/24 16:00 |
| S14 8 | 2 | "5338975".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 07:33 |
| S14 9 | 189 | (barrier adj layer) and (plug adj hole) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 07:34 |
| S15 0 | 111 | S149 and (ti or TiN) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 07:44 |
| S15 1 | 80 | S150 and ((chemical adj vapor adj deposition) or CvD) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 11:40 |
| S15 2 | 450 | (instection or examination) and rework | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 07:58 |
| S15 3 ⌐ | 114 | S152 and wafers | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 07:59 |
| S15 4 | 66 | S153 and etch | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 07:59 |

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| S15 5 | 0 | S154 and scrub | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 07:59 |
| S15 6 | 0 | S154 and sonics | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 07:59 |
| S15 7 | 0 | S154 and ultraonics | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 08:00 |
| S15 8 | 0 | S154 and meganics | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 08:01 |
| S15 9 | 2 | "5,338,975".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 08:45 |
| S16 0 | 88 | (contaminant or particle or (killer adj defect)) near barrier adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 08:46 |
| S16 1 | 7 | S160 and detect | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 08:47 |
| S16 2 | 0 | S161 and (examine or inspect) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 08:47 |
| S16 3 | 59 | semiconductor adj inspection adj methods | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 08:48 |
| S16 4 | 9 | S163 and electron | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 09:39 |

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| S16 5 | 2 | "4,822,753".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 09:44 |
| S16 6 | 784 | (etch adj (barrier or titanium)) and solution | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 09:45 |
| S16 7 | 643 | S166 and barrier | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 09:45 |
| S16 8 | 211 | S167 and (wet adj etch) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 09:45 |
| S16 9 | 112 | S168 and titanium | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 09:46 |
| S17 0 | 131 | S168 and interconnect | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 09:46 |
| S17 1 | 86 | S169 and interconnect | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 09:47 |
| S17 2 | 14 | S171 and sulfuric | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 09:49 |
| S17 3 | 11 | S171 and (phosphoric or H3PO4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 09:50 |
| S17 4 | 2 | "5514622".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 11:37 |

| S17 5 | 189 | (barrier adj layer) and (plug adj hole) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 12:34 |
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| S17 6 | 111 | S175 and (ti or TiN) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 11:40 |
| S17 7 | 80 | S176 and ((chemical adj vapor adj deposition) or CvD) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 11:40 |
| S17 8 | 29 | S177 and polysilicon | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 12:00 |
| S17 9 | 5 | S178 and Ti/TiN | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 12:32 |
| S18 0 | 92840 | S179 ans silicide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 12:32 |
| S18 1 | 3 | S179 and silicide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 12:32 |
| S18 2 | 10 | S175 and silicide near formation | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 13:06 |
| S18 3 | 2 | "5633111".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 13:06 |
| S18 4 | 187570 | (phosphoric adj acid) or H3PO4 or "H. sub.3PO.sub.4" or "H.sub.xPO.sub.x" or "H.sub.nPO.sub.n" or "H.sub.xPO. sub.n" or "H.sub.nPO.sub.x" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 13:35 |

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| S18 5 | 100101 | (Nitric adj acid) or (HNO3 or HNOx or HNOn or HNOsubx or HNOsubn or "HNO.subx" or "HNO.subn" or "HNO.sub.x" or "HNO.sub.n") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 13:35 |
| S18 6 | 260718 | (acetic adj acid) or (CH3COOH or CH3COOHChsub3COOH or "CH.sub.3. COOH" or CHxCOOH or "CH.sub.x. COOH" or CHsubxCOOH) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 13:38 |
| S18 7 | 3681296 | water or aqueous or H2O or (H2O or HxO or HnO or "H.sub2O" or "H. subxO" or "H.subnO" or "H.sub.2.O" or "H.sub.x.O" or "H.sub.n.O") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 13:39 |
| S18 8 | 21249 | S184 and S185 and S186 and S187 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 13:39 |
| S18 9 | 130 | S184 near S185 near S186 near S187 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 13:39 |
| S19 0 | 1169 | S188 and etch | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 13:40 |
| S19 1 | 65 | S189 and etch | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 13:40 |
| S19 2 | 57 | S191 and metal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 13:40 |
| S19 3 | 30 | S192 and titanium | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 15:59 |
| S19 4 | 4 | "6362027".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 17:04 |

| S195 | 2 | "5,598,284".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 15:59 |
| S196 | 5 | "6,613,614".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/27 17:05 |